



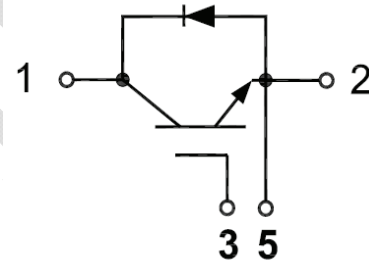
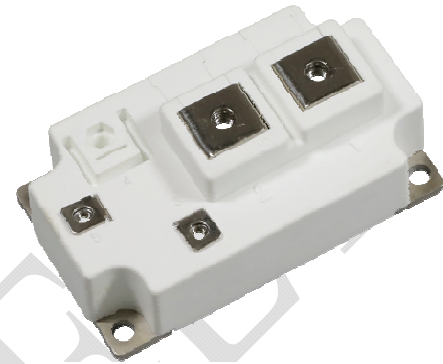
GT400SD120T2ZH

IGBT Module

Preliminary Data

Features:

- Field Stop Trench Gate IGBT
- Short Circuit Rated >10 μ s
- Low Saturation Voltage
- Low Switching Loss
- 100% RBSOA Tested(2 \times I_c)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Induction Heating
- UPS Systems
- High Power converters

IGBT, Inverter

Maximum Rated Values of IGBT(T_C=25 $^{\circ}$ C unless otherwise specified)

V _{CES}	Collector-Emitter Blocking Voltage		1200	V
V _{GES}	Gate-Emitter Voltage		\pm 20	V
I _C	Continuous Collector Current	T _C = 100 $^{\circ}$ C	400	A
		T _C = 25 $^{\circ}$ C	750	A
I _{CM}	Repetitive Peak Collector Current	T _J = 175 $^{\circ}$ C	800	A
t _{SC}	Short Circuit Withstand Time		>10	μ s
P _D	Maximum Power Dissipation per IGBT	T _C = 25 $^{\circ}$ C T _{Jmax} = 175 $^{\circ}$ C	2585	W



Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=4\text{mA}, V_{CE}=V_{GE}$	5.0	5.6	6.6	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=400\text{A}, V_{GE}=15\text{V}$	$T_J=25^\circ\text{C}$	1.70		V
			$T_J=125^\circ\text{C}$	1.90		V
			$T_J=150^\circ\text{C}$	2.00		
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}, V_{CE}=V_{CES}, T_J=25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=\pm 20\text{V}, V_{CE}=0\text{V}, T_J=25^\circ\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		34		nF
C_{res}	Reverse Transfer Capacitance			1.14		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}, I_C=400\text{A}, R_{Gon}=1\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	0.44		μs
			$T_J=125^\circ\text{C}$	0.45		
			$T_J=150^\circ\text{C}$	0.45		
t_r	Rise Time	$V_{CC}=600\text{V}, I_C=400\text{A}, R_{Goff}=1\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	0.15		μs
			$T_J=125^\circ\text{C}$	0.16		
			$T_J=150^\circ\text{C}$	0.16		
$t_{d(off)}$	Turn-off Delay Time	$V_{CC}=600\text{V}, I_C=400\text{A}, R_{Goff}=1\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	0.43		μs
			$T_J=125^\circ\text{C}$	0.46		
			$T_J=150^\circ\text{C}$	0.47		
t_f	Fall Time	$V_{CC}=600\text{V}, I_C=400\text{A}, R_{Goff}=1\Omega, V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	0.12		μs
			$T_J=125^\circ\text{C}$	0.16		
			$T_J=150^\circ\text{C}$	0.18		
E_{on}	Turn-on Switching Loss	$V_{CC}=600\text{V}, I_C=400\text{A}, R_{Gon}=1\Omega, V_{GE}=\pm 15\text{V},$ $di/dt=2056\text{A}/\mu\text{s} (T_J=150^\circ\text{C})$ Inductive Load	$T_J=25^\circ\text{C}$	28		mJ
			$T_J=125^\circ\text{C}$	39.8		
			$T_J=150^\circ\text{C}$	42.7		



E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =400A, R _{Goff} =1Ω, V _{GE} = ±15V, du/dt=3115V/μs (T _J =150°C) Inductive Load	T _J =25°C	39.1	mJ
			T _J =125°C	51.2	
			T _J =150°C	54.6	
Q _g	Total Gate Charge	V _{GE} =+15V...-15V	T _J =25°C	2.18	μC
R _{g internal}	Internal Gate Resistance		T _J =25°C	2.49	Ω
RBSOA	I _C =800A, V _{CC} =1050V, V _p =1200V, R _{Goff} = 1Ω, V _{GE} =+15V to 0V, T _J =150°C			Trapezoid	
I _{SC}	SC Data	V _{GE} =± 15V, V _{CC} =600V, R _{Gon} =1Ω, R _{Goff} =1Ω, tp=10us , Inductive Load, T _J =150°C		1931	A
R _{θJC}	IGBT Thermal Resistance: Junction-To-Case(per leg)			0.058	°C/W

Diode, Inverter

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	1200	V
I _F	Diode Continuous Forward Current	400	A
I _{FM}	Diode Maximum Forward Current	800	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V _{FM}	Forward Voltage	I _F =400A	T _J =25°C	2.20		V
			T _J =125°C	2.30		
			T _J =150°C	2.20		
t _{rr}	Reverse Recovery Time	I _F =400A, -diF/dt =2380A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C	0.30		μs
			T _J =125°C	0.47		
			T _J =150°C	0.55		
I _{rr}	Peak Reverse Recovery Current	I _F =400A, -diF/dt =2380A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C	262		A
			T _J =125°C	325		
			T _J =150°C	344		



Q _{rr}	Reverse Recovery Charge	I _F =400A, -diF/dt =2380A/μs(T _J =15°C0), V _R =600V, V _{GE} =-15V	T _J =25°C	21.5	μC
			T _J =125°C	40.0	
			T _J =150°C	46.4	
E _{rec}	Reverse Recovery Energy		T _J =25°C	8.55	mJ
			T _J =125°C	17.27	
			T _J =150°C	20.15	
R _{θJC}	Diode Thermal Resistance: Junction-To-Case (per leg)		0.097	°C/W	

Module

Symbol	Description	Min	Typ	Max	Unit
V _{iso}	Isolation Voltage (All Terminals Shorted)	RMS, f = 50Hz, 1minute	2.5		kV
Internal Isolation			Al2O3		
Material of Module Baseplate			Copper		
d _{creep}	Terminal to Heatsink		25		mm
	Terminal to Terminal		19		mm
d _{clear}	Terminal to Heatsink		25		mm
	Terminal to Terminal		10		mm
L _{sCE}	Stray Inductance Module		16		nH
T _J	Maximum Junction Temperature			175	°C
T _{JOP}	Maximum Operating Junction Temperature Range	-40		+150	°C
T _{stg}	Storage Temperature	-40		+125	°C
CTI	Comparative Tracking Index	200			
R _{θCS}	Case-To-Sink Thermally (Conductive Grease Applied)		0.03		°C/W
T	Signal Terminals Screw:M4	1.1		2.0	N·m
	Power Terminals Screw:M6	2.5		5.0	N·m
T	Mounting Screw:M6	3.0		6.0	N·m
G	Weight		320		g

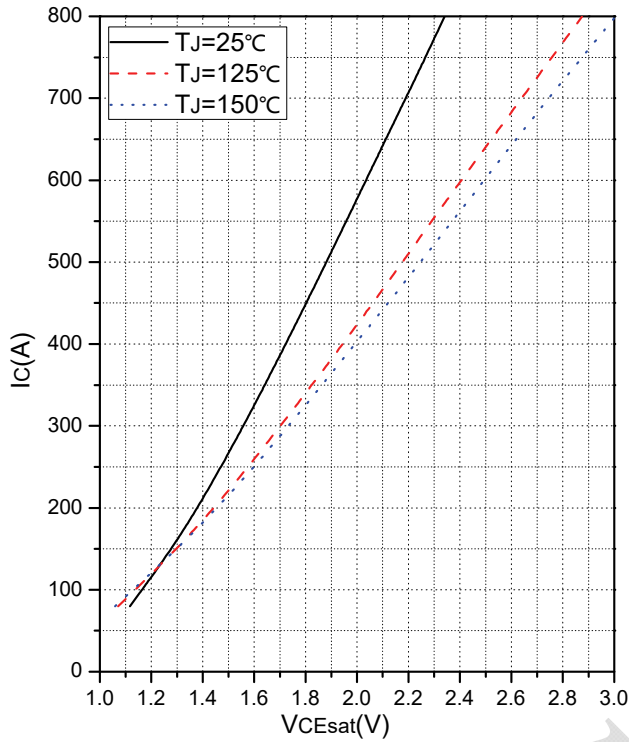


Fig.1 Typical Saturation Voltage Characteristics

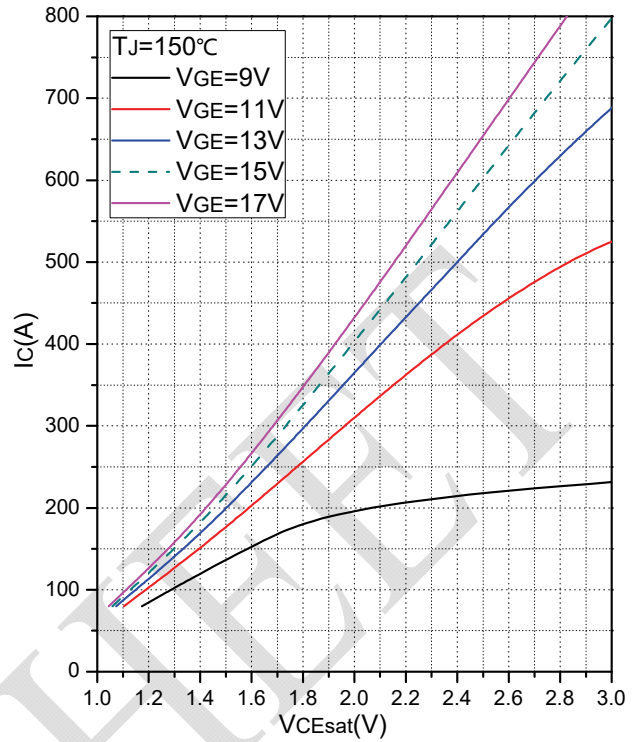


Fig.2 Typical Output Characteristics

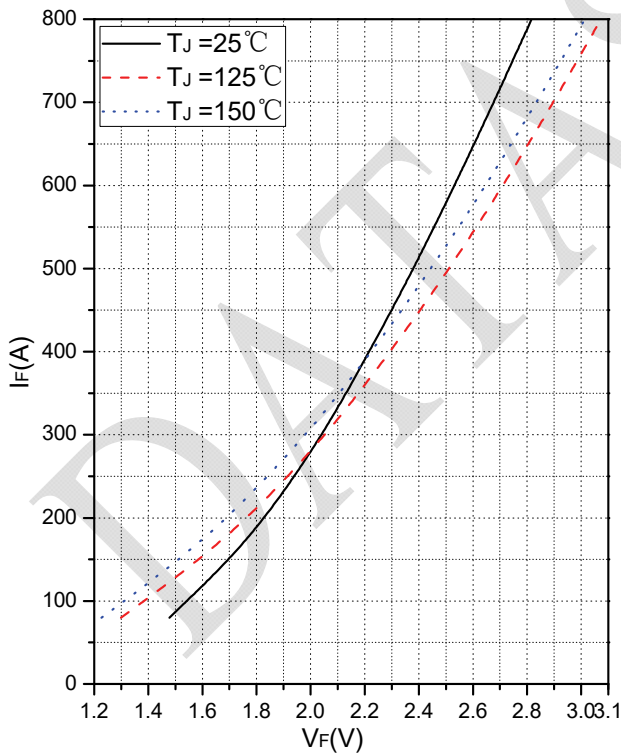


Fig.3 Forward Characteristics of Diode

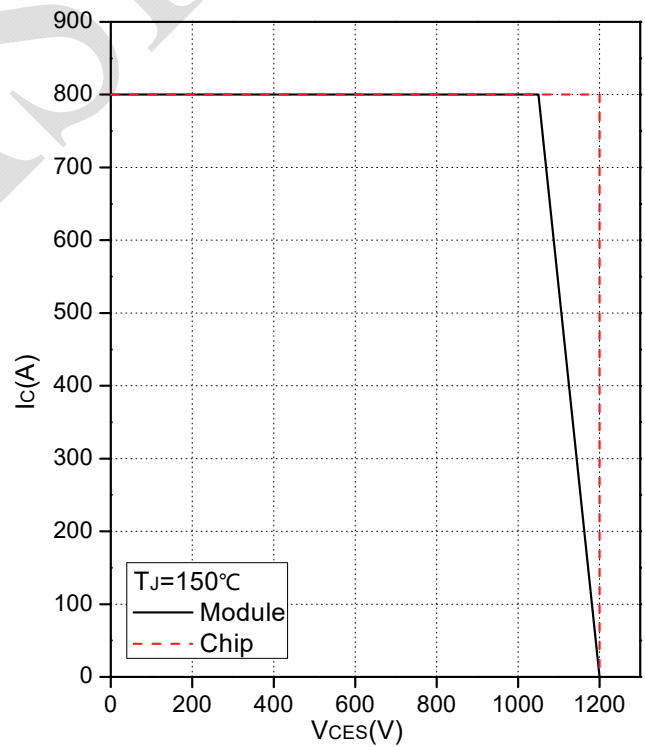


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

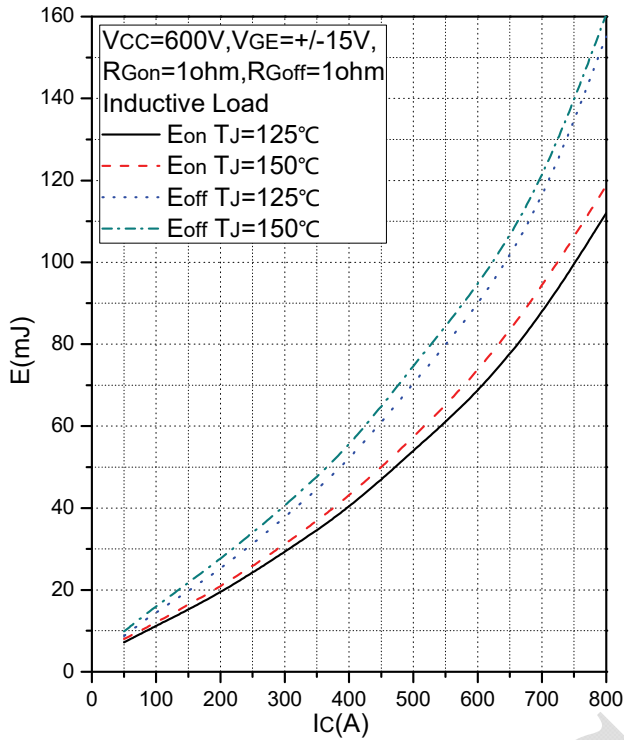


Fig.5 Typical Switching Loss vs. Collector Current

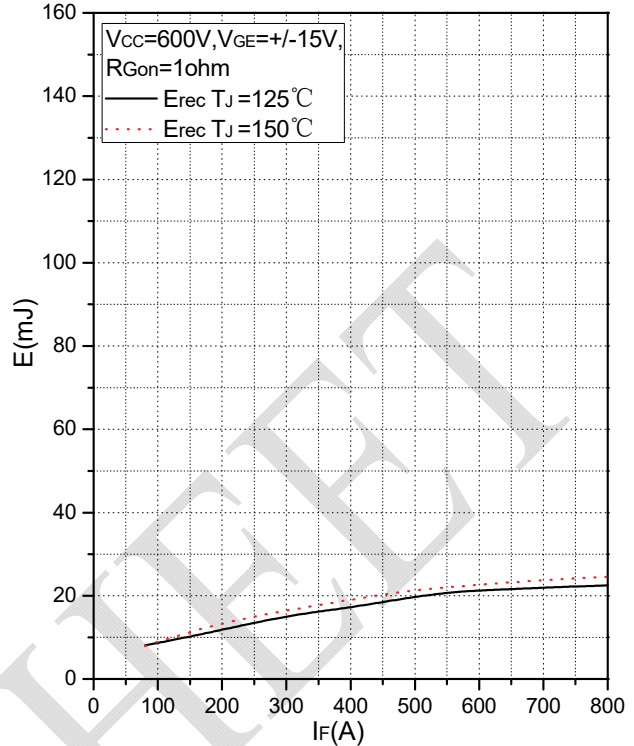


Fig.6 Typical Switching Loss vs. Forward Current

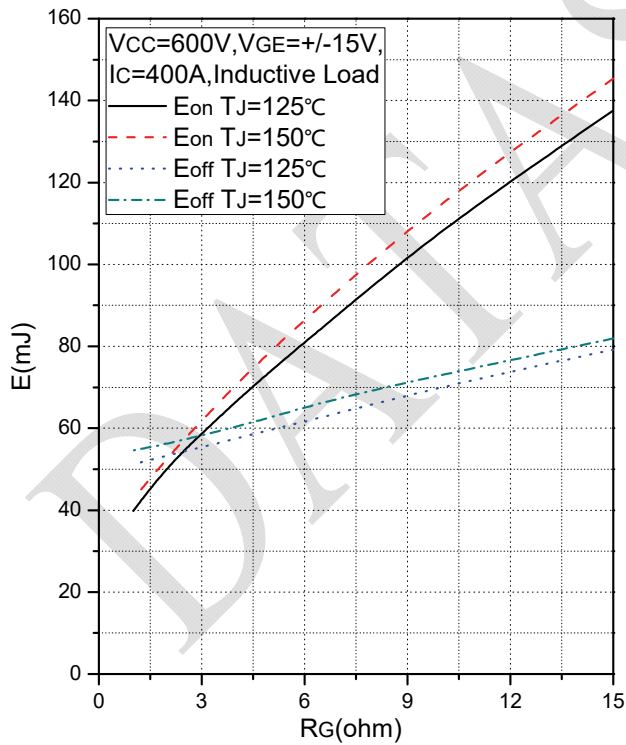


Fig.7 Typical Switching Loss vs. Gate Resistance

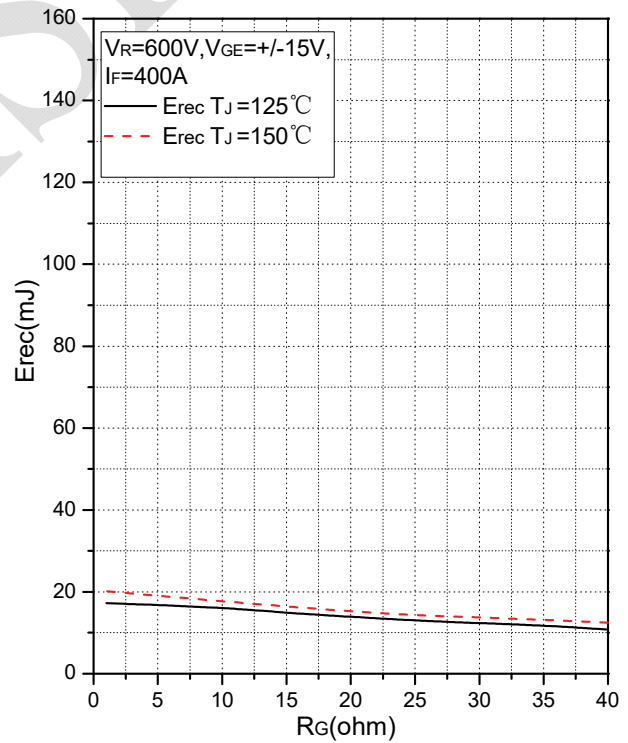


Fig.8 Typical Switching Loss vs. Gate Resistance

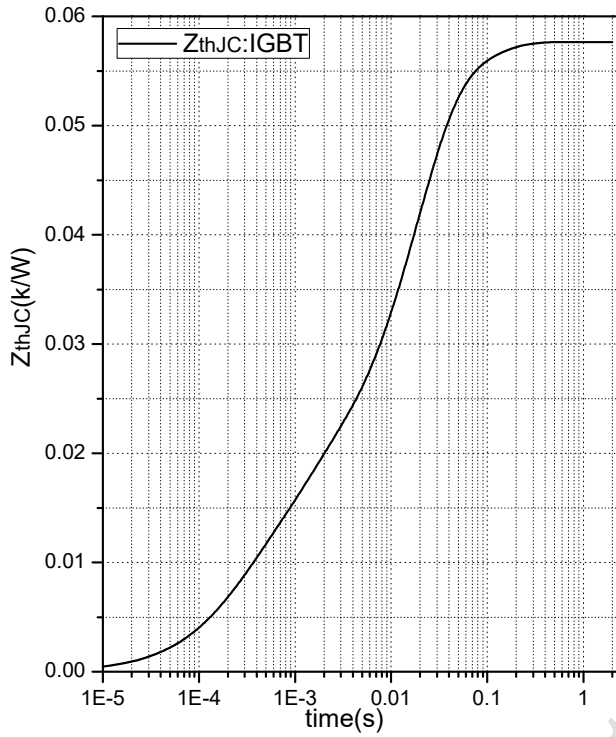


Fig.9 Transient Thermal Impedance (IGBT)

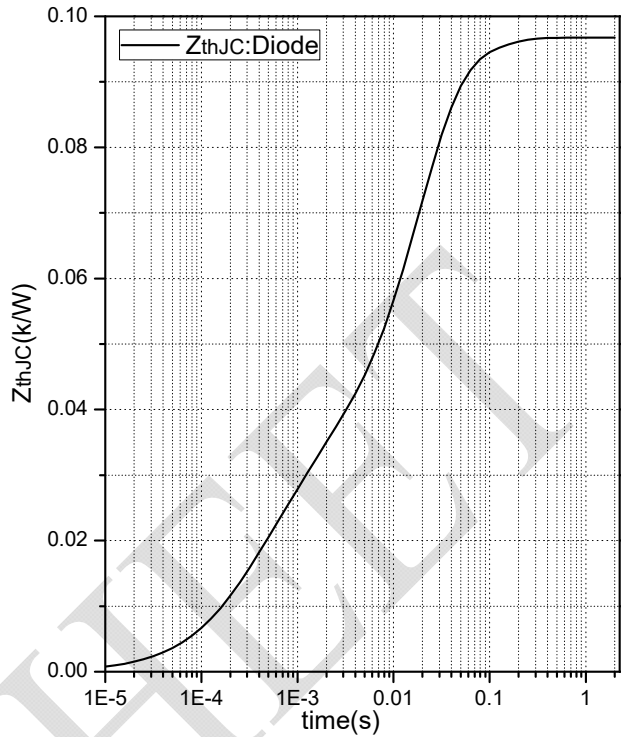
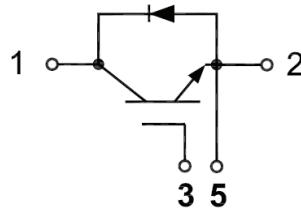


Fig.10 Transient Thermal Impedance (Diode)

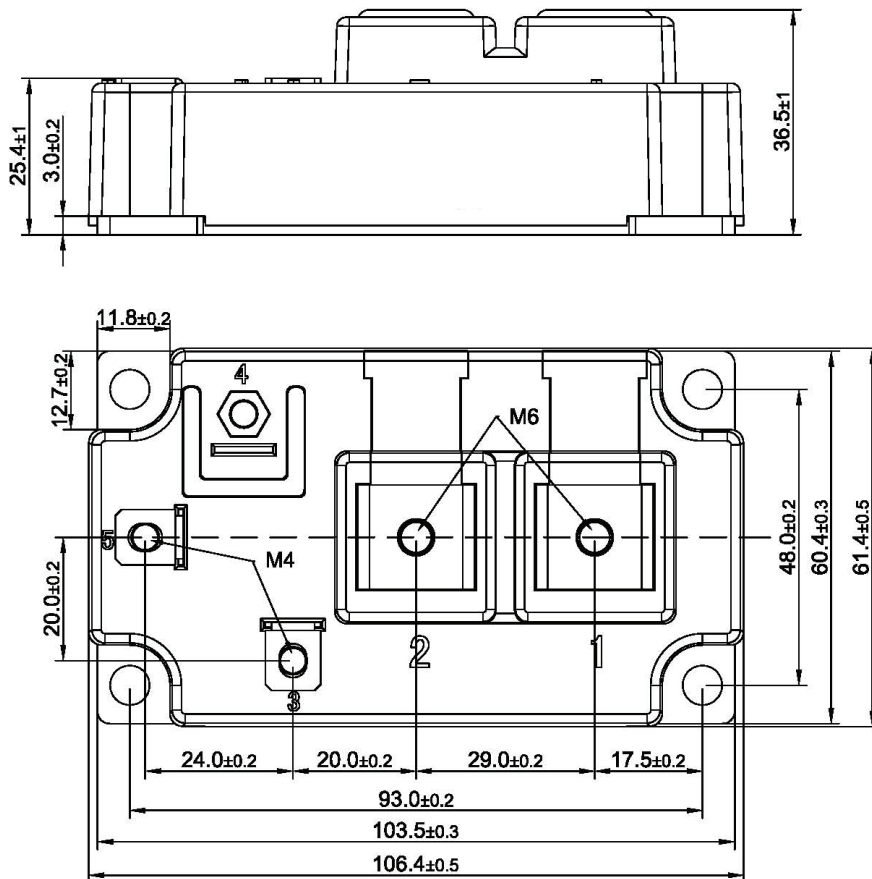
DATA SHEET



Internal Circuit



Package Outline (Unit: mm):





Date	Revision	Notes
08/06/2019	01	Initial Release

Announcement

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